

SEMIPACK<sup>®</sup> 3

### **Thyristor Modules**

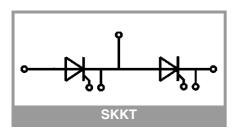
#### SKKT 273/16 E

#### Features\*

- Industrial standard package
- Electrically insulated base plate
- Heat transfer through aluminum oxide ceramic insulated metal base plate
- Chip soldered on direct copper bonded Al<sub>2</sub>O<sub>3</sub> ceramic
- UL recognition, file no. E63532

#### **Typical Applications**

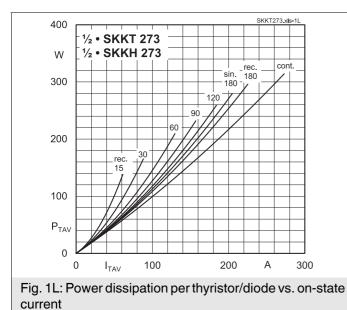
- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

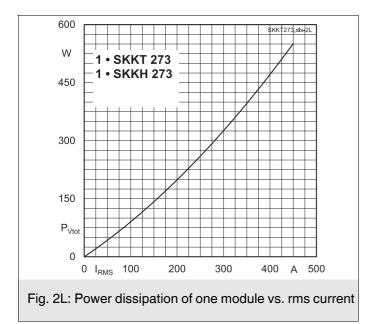


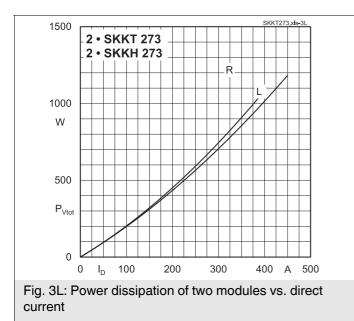
Absolute	e Maximum Ratin	gs				
Symbol	Conditions	Values			Unit	
Chip						
I <sub>T(AV)</sub>	sinus 180°	T <sub>c</sub> = 85 °C	274			Α
		T <sub>c</sub> = 100 °C		204		Α
I <sub>TSM</sub>	10 ms	T <sub>j</sub> = 25 °C		9000		
		T <sub>j</sub> = 130 °C		8000		
i <sup>2</sup> t	10 ms	T <sub>j</sub> = 25 °C		405000		
		T <sub>j</sub> = 130 °C		320000		
V <sub>RSM</sub>			1700		V	
V <sub>RRM</sub>			1600		V	
V <sub>DRM</sub>			1600		V	
(di/dt) <sub>cr</sub>	T <sub>j</sub> = 130 °C		130			A/μs
(dv/dt) <sub>cr</sub>	T <sub>j</sub> = 130 °C			1000		V/µs
Tj				-40 130		
Module						
T <sub>stg</sub>			-40 125		°C	
V <sub>isol</sub>		1 min		3000		V
	a.c.; 50 Hz; r.m.s.	1 s		3600	V	
Characte						
Characte	1		min	tun	mov	linit
Symbol	eristics Conditions	-	min.	typ.	max.	Unit
Symbol Chip	Conditions	50.0	min.	typ.		
Symbol Chip V <sub>T</sub>	Conditions $T_j = 25 \text{ °C}, I_T = 75$	50 A	min.	typ.	1.6	V
Symbol Chip V <sub>T</sub> V <sub>T(TO)</sub>	Conditions $T_j = 25 \ ^{\circ}C, I_T = 75$ $T_j = 130 \ ^{\circ}C$	50 A	min.	typ.	1.6 0.90	V V
Symbol           Chip           V <sub>T</sub> V <sub>T(TO)</sub> r <sub>T</sub>	Conditions $T_j = 25 \ ^\circ C, I_T = 75$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C$		min.	typ.	1.6 0.90 0.92	V V mΩ
Symbol           Chip           V <sub>T</sub> V <sub>T(TO)</sub> r <sub>T</sub> I <sub>DD</sub> ;I <sub>RD</sub>	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{T} = 75 \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C, \ V_{DD} = 100 \\ \hline T_{j} = 100 \ ^{\circ}C, \ T_{j} = 100 \ ^{\circ}C, \ T_{j} = 100 \\ \hline T_{j} = 100 \ ^{\circ}C, \ T_{j} =$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub>	min.		1.6 0.90	V V mΩ mA
Symbol Chip V <sub>T</sub> V <sub>T(TO)</sub> r <sub>T</sub> I <sub>DD</sub> ;I <sub>RD</sub> t <sub>gd</sub>	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline $T_j = 25 $ ^{\circ}C, $I_T = 75$ \\ \hline $T_j = 130 $ ^{\circ}C$ \\ \hline $T_j = 130 $ ^{\circ}C$ \\ \hline $T_j = 130 $ ^{\circ}C, $V_{DD} = $T_j = 25 $ ^{\circ}C, $I_G = 1$ \\ \hline $T_j = 25 $ ^{\circ}C, $I_G = 1$ \\ \hline $T_j = 100 $ $ ^{\circ}C, $T_{DD} = $T_{DD} $ $ ^{\circ}C, $ $	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	min.	1	1.6 0.90 0.92	V V mΩ mA μs
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline $T_j = 25 \ ^\circ C, \ I_T = 75 \\ \hline $T_j = 130 \ ^\circ C $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	min.	1 2	1.6 0.90 0.92	V V mΩ mA μs μs
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgq           tgr	$\label{eq:transform} \begin{array}{ c c c c } \hline Conditions \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{T} = 75 \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C, \ V_{DD} = 1 \\ \hline V_{D} = 0.67 \ ^{*}V_{DRM} \\ \hline T_{j} = 130 \ ^{\circ}C \end{array}$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	min.	1 2 150	1.6 0.90 0.92 100	V V mΩ mA μs μs μs
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           tq           IH	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline $T_j = 25 \ ^\circ C, \ $I_T = 75$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C, \ $V_{DD} = 1$ \\ \hline $T_j = 25 \ ^\circ C, \ $I_G = 1$ \\ \hline $V_D = 0.67 \ ^* \ $V_{DRM}$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 25 \ ^\circ C$ \\ \hline \end{tabular}$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	min.	1 2 150 150	1.6 0.90 0.92 100 500	V V mΩ mA μs μs mA
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           tq           IH           L	$\label{eq:conditions} \left  \begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C}, \ I_{T} = 75 \\ T_{j} = 130 \ ^{\circ}\text{C} \\ T_{j} = 130 \ ^{\circ}\text{C} \\ T_{j} = 130 \ ^{\circ}\text{C}, \ V_{DD} = 125 \ ^{\circ}\text{C}, \ I_{G} = 125 \ ^{\circ}\text{C} \\ V_{D} = 0.67 \ ^{*}\text{V}_{DRM} \\ T_{j} = 130 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C}, \ R_{G} = 325 \ ^{\circ}\text{C} \\ T_{j} = 25 \ ^{\circ}\text{C} \ T_{j} = 25 $	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs		1 2 150	1.6 0.90 0.92 100	V V mΩ mA μs μs mA mA
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           tq           IH           L           VGT	$\label{eq:conditions} \begin{bmatrix} T_j = 25 \ ^\circ C, \ I_T = 75 \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C, \ V_{DD} = 125 \ ^\circ C, \ I_G = 125 \\ V_D = 0.67 \ ^* \ V_{DRM} \\ T_j = 130 \ ^\circ C \\ T_j = 25 \ ^\circ C, \ R_G = 35 \\ T_j = 25 \ ^\circ C, \ R_G = 35 \\ T_j = 25 \ ^\circ C, \ d.c. \end{bmatrix}$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	2	1 2 150 150	1.6 0.90 0.92 100 500	V V mΩ mA μs μs mA mA V
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           tqr           IL           VGT           IGT	$\label{eq:conditions} \begin{bmatrix} T_j = 25 \ ^\circ C, \ I_T = 75 \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C, \ V_{DD} = 1 \\ T_j = 25 \ ^\circ C, \ I_G = 1 \\ V_D = 0.67 \ ^\ast \ V_{DRM} \\ T_j = 130 \ ^\circ C \\ T_j = 25 \ ^\circ C, \ T_j = 25 \ ^\circ C, \ R_G = 3 \\ T_j = 25 \ ^\circ C, \ R_G = 3 \\ T_j = 25 \ ^\circ C, \ d.c. \\ T_j = 25 \ ^\circ C, \ d.c. \\ \end{bmatrix}$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs		1 2 150 150	1.6 0.90 0.92 100 500 2000	V V mΩ mA μs μs mA mA V V
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           IL           VGT           IGT           IGT	$\label{eq:conditions} \hline $T_j = 25 \ ^\circ C, \ I_T = 75$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C, \ V_{DD} = 1$ \\ \hline $T_j = 25 \ ^\circ C, \ I_G = 1$ \\ \hline $V_D = 0.67 \ ^* \ V_{DRM}$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 25 \ ^\circ C$ \\ \hline $T_j = 25 \ ^\circ C, \ R_G = 3$ \\ \hline $T_j = 25 \ ^\circ C, \ d.c.$ \\ \hline $T_j = 25 \ ^\circ C, \ d.c.$ \\ \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline $T_j = 100 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline \hline $T_j = 100 \ ^\circ C, \ d.c.$ \\ \hline $	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs	2	1 2 150 150	1.6 0.90 0.92 100 500 2000	V V mΩ μs μs μs mA mA V mA V
Symbol Chip V <sub>T</sub> V <sub>T(TO)</sub> r <sub>T</sub> l <sub>DD</sub> ;l <sub>RD</sub> t <sub>gd</sub> t <sub>gd</sub> t <sub>gr</sub> t <sub>q</sub> l <sub>H</sub> l <sub>L</sub> V <sub>GT</sub> l <sub>GT</sub> l <sub>GD</sub>	$\label{eq:conditions} \begin{bmatrix} T_j = 25 \ ^\circ C, \ I_T = 75 \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C, \ V_{DD} = 1 \\ T_j = 25 \ ^\circ C, \ I_G = 1 \\ V_D = 0.67 \ ^\ast \ V_{DRM} \\ T_j = 130 \ ^\circ C \\ T_j = 25 \ ^\circ C, \ T_j = 25 \ ^\circ C, \ R_G = 3 \\ T_j = 25 \ ^\circ C, \ R_G = 3 \\ T_j = 25 \ ^\circ C, \ d.c. \\ T_j = 25 \ ^\circ C, \ d.c. \\ \end{bmatrix}$	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs 33 Ω	2	1 2 150 150	1.6 0.90 0.92 100 500 2000 0.25 10	V V mΩ μs μs mA mA V mA V mA
Symbol           Chip           VT           VT(TO)           rT           IDD;IRD           tgd           tgr           IL           VGT           IGT           IGT	$\label{eq:conditions} \hline $T_j = 25 \ ^\circ C, \ I_T = 75$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 130 \ ^\circ C, \ V_{DD} = 1$ \\ \hline $T_j = 25 \ ^\circ C, \ I_G = 1$ \\ \hline $V_D = 0.67 \ ^* \ V_{DRM}$ \\ \hline $T_j = 130 \ ^\circ C$ \\ \hline $T_j = 25 \ ^\circ C$ \\ \hline $T_j = 25 \ ^\circ C, \ R_G = 3$ \\ \hline $T_j = 25 \ ^\circ C, \ d.c.$ \\ \hline $T_j = 25 \ ^\circ C, \ d.c.$ \\ \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline $T_j = 130 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline $T_j = 100 \ ^\circ C, \ d.c.$ \\ \hline \hline \hline \hline $T_j = 100 \ ^\circ C, \ d.c.$ \\ \hline $	= V <sub>DRM</sub> ; V <sub>RD</sub> = V <sub>RRM</sub> A, di <sub>G</sub> /dt = 1 A/μs 33 Ω	2	1 2 150 150	1.6 0.90 0.92 100 500 2000 0.25 10 0.104	V V mΩ mA μs μs mA mA V mA V mA
Symbol Chip V <sub>T</sub> V <sub>T(TO)</sub> r 1 <sub>DD</sub> ;I <sub>RD</sub> t <sub>gd</sub> t <sub>gr</sub> t <sub>q</sub> t <sub>q</sub> I <sub>H</sub> I <sub>L</sub> V <sub>GT</sub> I <sub>GD</sub> I <sub>GD</sub> R <sub>th(j-c)</sub>	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline $T_j = 25 \ ^\circ C, \ I_T = 75 \\ \hline $T_j = 130 \ ^\circ C $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $	$= V_{DRM}; V_{RD} = V_{RRM}$ A, di <sub>G</sub> /dt = 1 A/µs 33 Ω per chip per module	2	1 2 150 150	1.6 0.90 0.92 100 500 2000 0.25 10 0.104 0.052	V V mΩ mA μs μs mA mA V mA V mA K/W
Symbol Chip V <sub>T</sub> V <sub>T(TO)</sub> r <sub>T</sub> l <sub>DD</sub> ;l <sub>RD</sub> t <sub>gd</sub> t <sub>gd</sub> t <sub>gr</sub> t <sub>q</sub> l <sub>H</sub> l <sub>L</sub> V <sub>GT</sub> l <sub>GT</sub> l <sub>GD</sub>	$\label{eq:conditions} \begin{bmatrix} T_j = 25 \ ^\circ C, \ I_T = 75 \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C \\ T_j = 130 \ ^\circ C, \ V_{DD} = 10 \\ T_j = 25 \ ^\circ C, \ I_G = 10 \\ V_D = 0.67 \ ^* \ V_{DRM} \\ T_j = 130 \ ^\circ C \\ T_j = 25 \ ^\circ C \\ T_j = 25 \ ^\circ C, \ R_G = 30 \\ T_j = 25 \ ^\circ C, \ d.c. \\ T_j = 25 \ ^\circ C, \ d.c. \\ T_j = 130 \ ^\circ C, \ d.c. \\ T_j = 130 \ ^\circ C, \ d.c. \\ T_j = 130 \ ^\circ C, \ d.c. \\ \end{bmatrix}$	$= V_{DRM}; V_{RD} = V_{RRM}$ A, di <sub>G</sub> /dt = 1 A/µs 33 Ω per chip per module per chip	2	1 2 150 150	1.6 0.90 0.92 100 500 2000 0.25 10 0.104 0.052 0.108	V           W           mA           μs           μs           mA           V           mA           K/W           K/W
Symbol Chip V <sub>T</sub> V <sub>T</sub> (TO) r I <sub>DD</sub> ;I <sub>RD</sub> t <sub>gd</sub> t <sub>gr</sub> t <sub>q</sub> t <sub>q</sub> I <sub>H</sub> I <sub>L</sub> V <sub>GT</sub> I <sub>GD</sub> I <sub>GD</sub> R <sub>th(j-c)</sub>	$\begin{tabular}{ c c c c } \hline Conditions \\ \hline $T_j = 25 \ ^\circ C, \ I_T = 75 \\ \hline $T_j = 130 \ ^\circ C $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $ $	$= V_{DRM}; V_{RD} = V_{RRM}$ A, di <sub>G</sub> /dt = 1 A/µs 33 Ω per chip per module	2	1 2 150 150	1.6 0.90 0.92 100 500 2000 0.25 10 0.104 0.052	V           W           mΩ           μs           μs           mA           V           mA           K/W

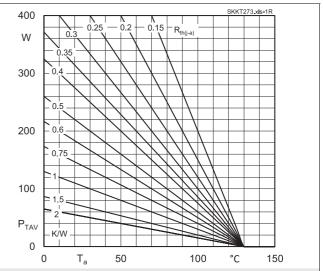
## Module

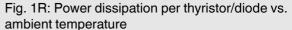
Module					
R <sub>th(c-s)</sub>	chip		0.08		K/W
	module		0.04		K/W
Ms	to heatsink M5	4.25		5.75	Nm
Mt	to terminals M8	7.65		10.35	Nm
а				5 * 9.81	m/s²
w			410		g

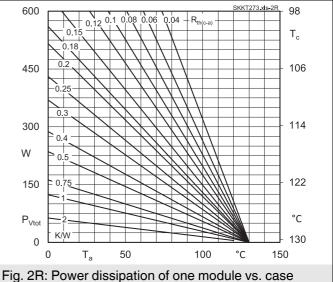












temperature

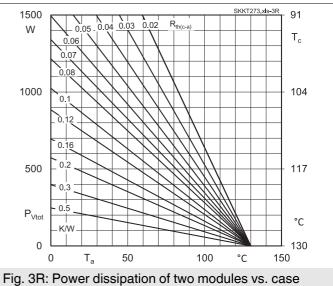
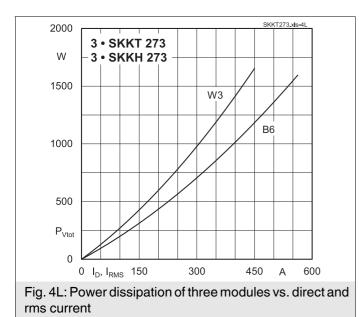
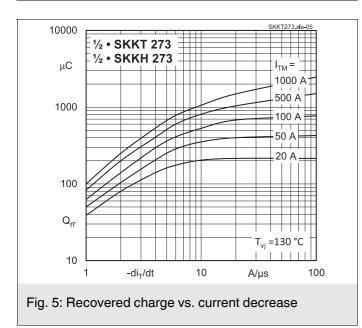
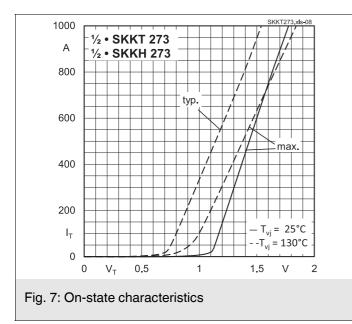


Fig. 3R: Power dissipation of two modules vs. case temperature







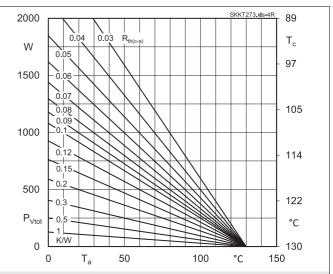


Fig. 4R: Power dissipation of three modules vs. case temperature

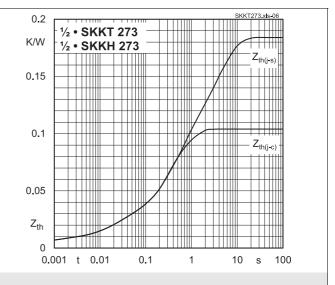
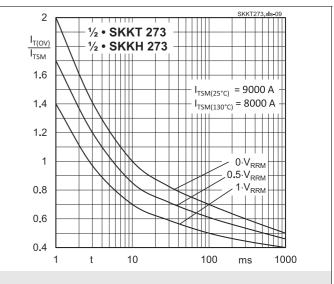
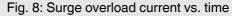
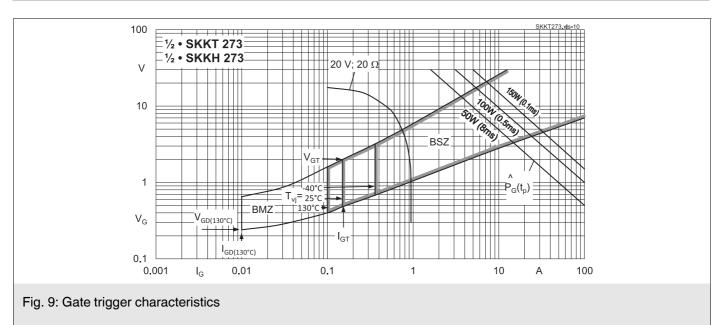
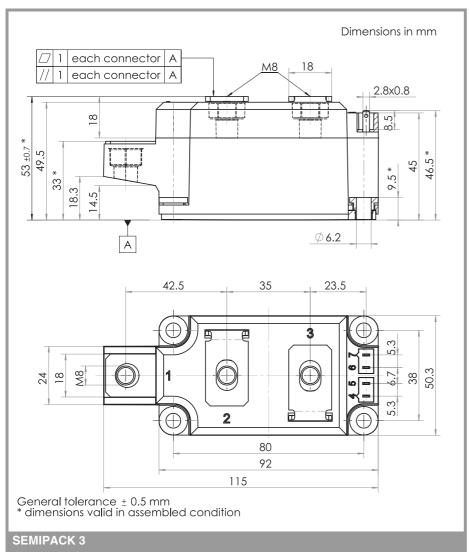


Fig. 6: Transient thermal impedance vs. time









This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

### \*IMPORTANT INFORMATION AND WARNINGS

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in

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